L Number	Hits	Search Text	DB	Time stamp
1	4	6211094.URPN.	USPAT	2004/07/11
2	5	("3627569" "5131752" "5318632" "5800616" "6054181").PN.	USPAT	12:30 2004/07/11 12:36
3	71	5131752.URPN.	USPAT	2004/07/11
4	4	6211094.URPN.	USPAT	2004/07/11
5	5	("3627569" "5131752" "5318632" "5800616" "6054181").PN.	USPAT	2004/07/11
6	17		USPAT	2004/07/11
7	4	("4198261" "5131752" "5160576" "5270222").PN.	USPAT	2004/07/11
8	0	5300313.URPN.	USPAT	2004/07/11
9	0	5300313.URPN.	USPAT	2004/07/11
10	5	("2726173" "4427711" "4466872" "5131752" "5204144").PN.	USPAT	2004/07/11
11	8	("3158675" "4105338" "4649261" "4695162" "4698486" "4837603"	USPAT	2004/07/11 13:10
16	3525	"4850711" "4906844").PN. method with control with thickness with (film layer)	USPAT; US-PGPUB;	2004/07/11 14:18
17	205	(method with control with thickness with (film layer)) and determining and comparing	EPO; JPO USPAT; US-PGPUB;	2004/07/11 14:27
18	136	((method with control with thickness with (film layer)) and determining and	EPO; JPO USPAT; US-PGPUB;	2004/07/11 14:26
19	86	comparing) and (wafer semiconductor) (((method with control with thickness with (film layer)) and determining and comparing) and (wafer semiconductor)) and	EPO; JPO USPAT; US-PGPUB; EPO; JPO	2004/07/11 14:22
20	2024	adjusting (method with control with thickness with (film layer)) and (wafer semiconductor)	USPAT; US-PGPUB;	2004/07/11 14:26
21	1823	adjusting same determining same comparing	EPO; JPO USPAT; US-PGPUB;	2004/07/11 14:38
22	2	((method with control with thickness with (film layer)) and (wafer semiconductor)) and (adjusting same determining same comparing)	EPO; JPO USPAT; US-PGPUB; EPO; JPO	2004/07/11